

**6N70-C**

Preliminary

Power MOSFET**6.0A, 700V N-CHANNEL
POWER MOSFET****DESCRIPTION**

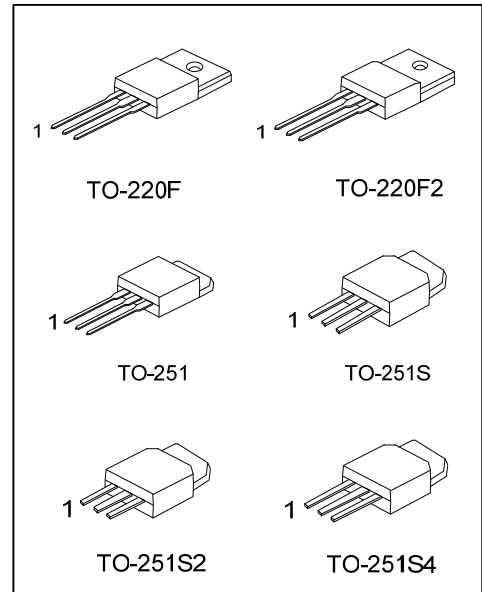
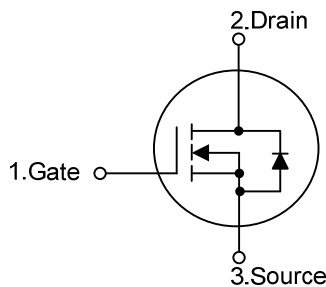
The UTC 6N70-C is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed, low gate charge and low input capacitance.

The UTC 6N70-C is universally applied in high efficiency switch mode power supply.

FEATURES

* $R_{DS(ON)} < 1.8\Omega$ @ $V_{GS}=10V$, $I_D=3A$

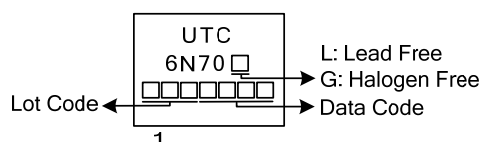
* High switching speed

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N70L-TF3-T	6N70G-TF3-T	TO-220F	G	D	S	Tube
6N70L-TF2-T	6N70G-TF2-T	TO-220F2	G	D	S	Tube
6N70L-TM3-T	6N70G-TM3-T	TO-251	G	D	S	Tube
6N70L-TMS-T	6N70G-TMS-T	TO-251S	G	D	S	Tube
6N70L-TMS2-T	6N70G-TMS2-T	TO-251S2	G	D	S	Tube
6N70L-TMS4-T	6N70G-TMS4-T	TO-251S4	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) T: Tube (2) TF3: TO-220F, TF2: TO-220F2, TM3: TO-251 TMS: TO-251S, TMS2: TO-251S2, TMS4: TO-251S4 (3) L: Lead Free, G: Halogen Free and Lead Free
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MARKING

■ **ABSOLUTE MAXIMUM RATINGS** (unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V _{DSS}	700	V
Gate-Source Voltage (Note 2)			V _{GSS}	±30	V
Drain Current	Continuous	T _C =25°C	I _D	6	A
		T _C =100°C		3.8	A
	Pulsed		I _{DM}	24	A
Avalanche Current (Note 2)			I _{AR}	6	A
Avalanche Energy	Single Pulsed (Note 3)		E _{AS}	108	mJ
	Repetitive (Note 2)		E _{AR}	13	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	2.5	V/ns
Power Dissipation	TO-220F		P _D	40	W
	TO-220F2			42	
	TO-251/TO-251S			55	
	TO-251S2/TO-251S4				
Linear Derarting Factor	TO-220F		P _D	0.32	W/°C
	TO-220F2			0.33	
	TO-251/TO-251S			0.44	
	TO-251S2/TO-251S4				
Junction Temperature			T _J	+150	°C
Storage Temperature			T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 6\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 27\Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD} \leq 6\text{A}$, $di/dt \leq 140\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F/TO-220F2	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-251S		110	$^{\circ}\text{C}/\text{W}$
	TO-251S2/TO-251S4			
Junction to Case	TO-220F	θ_{JC}	3.1	$^{\circ}\text{C}/\text{W}$
	TO-220F2		2.9	$^{\circ}\text{C}/\text{W}$
	TO-251/TO-251S		2.27	$^{\circ}\text{C}/\text{W}$
	TO-251S2/TO-251S4			

■ **ELECTRICAL CHARACTERISTICS** ($T_C=25^\circ\text{C}$, unless otherwise specified)

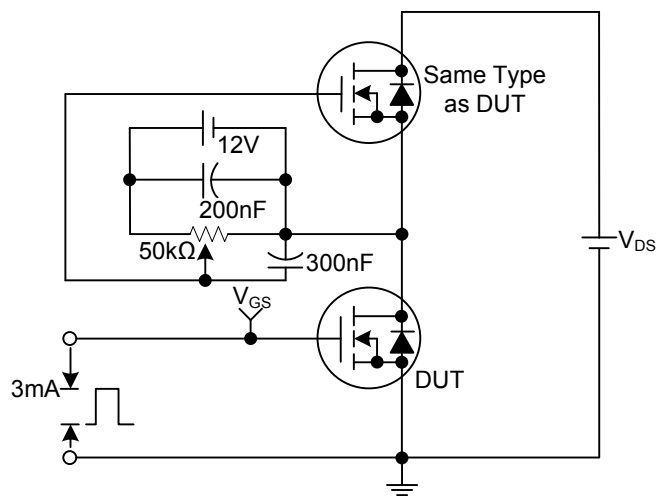
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	700			V
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA		0.79		V/°C
Drain-Source Leakage Current		I _{DSS}	V _{DS} =700V			25	μA
			V _{DS} =560V, T _C =125°C			250	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA, V _{DS} =5V	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =3A (Note 1)		1.5	1.8	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz (Note 1, 2)		700	1000	pF
Output Capacitance		C _{OSS}			79	120	pF
Reverse Transfer Capacitance		C _{RSS}			6	13	pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		t _{D(ON)}	V _{DD} =30V, I _D =1A, R _G =25Ω		55	75	ns
Rise Time		t _R			50	70	ns
Turn-OFF Delay Time		t _{D(OFF)}			180	210	ns
Fall-Time		t _F			50	70	ns
Total Gate Charge		Q _G	V _{GS} =10V, V _{DS} =50V, I _D =1.3A (Note 1, 2)		25	40	nC
Gate to Source Charge		Q _{GS}			6.5		nC
Gate to Drain Charge		Q _{GD}			4.8		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S	Integral reverse pn-diode in the MOSFET			6	A
Maximum Body-Diode Pulsed Current (Note 3)		I _{SM}				24	A
Drain-Source Diode Forward Voltage (Note 2)		V _{SD}	I _S =6A, V _{GS} =0V, T _J = 25°C			1.4	V

Notes: 1. Pulse Test: Pulse width $\leq 250\mu\text{s}$, Duty cycle $\leq 2\%$

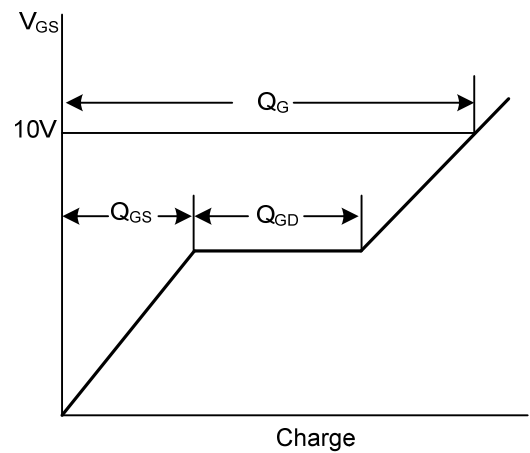
2. Essentially independent of operating temperature

3. Repetitive Rating: Pulse width limited by maximum junction temperature

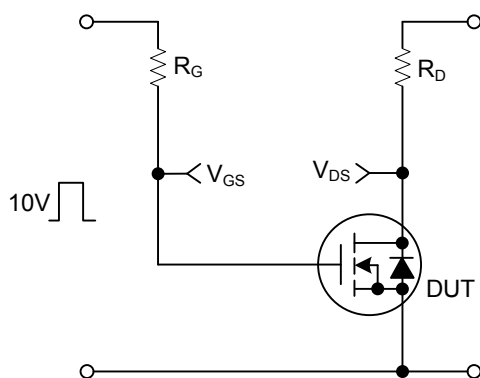
■ TEST CIRCUITS AND WAVEFORMS



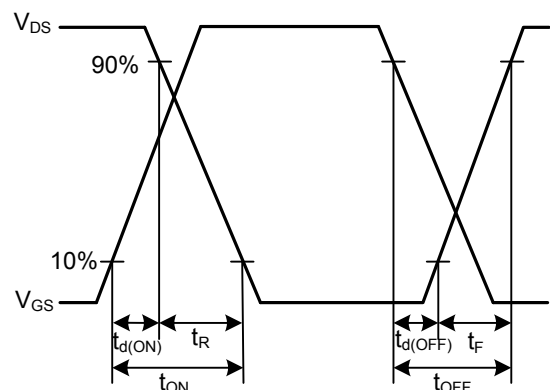
Gate Charge Test Circuit



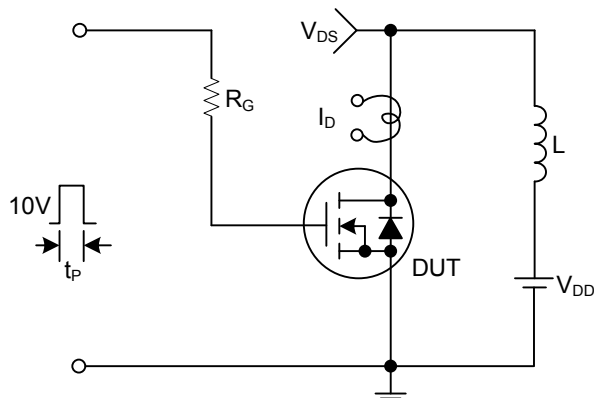
Gate Charge Waveforms



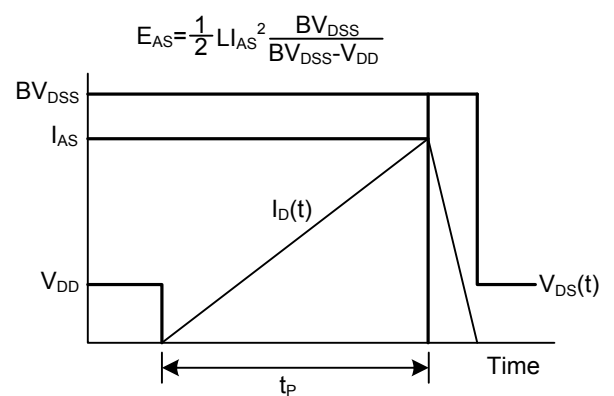
Resistive Switching Test Circuit



Resistive Switching Waveforms

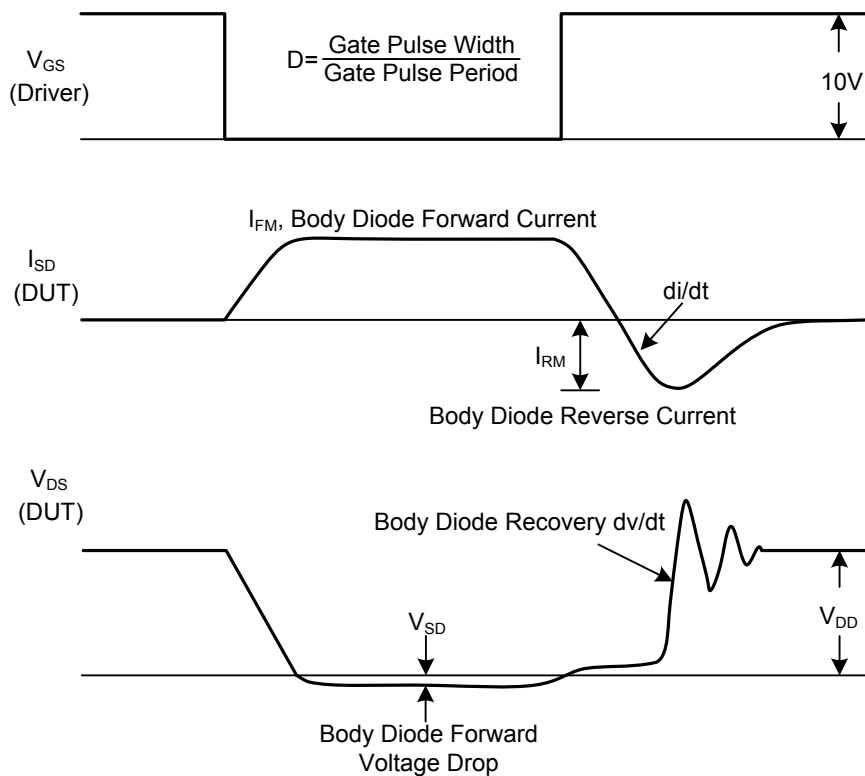
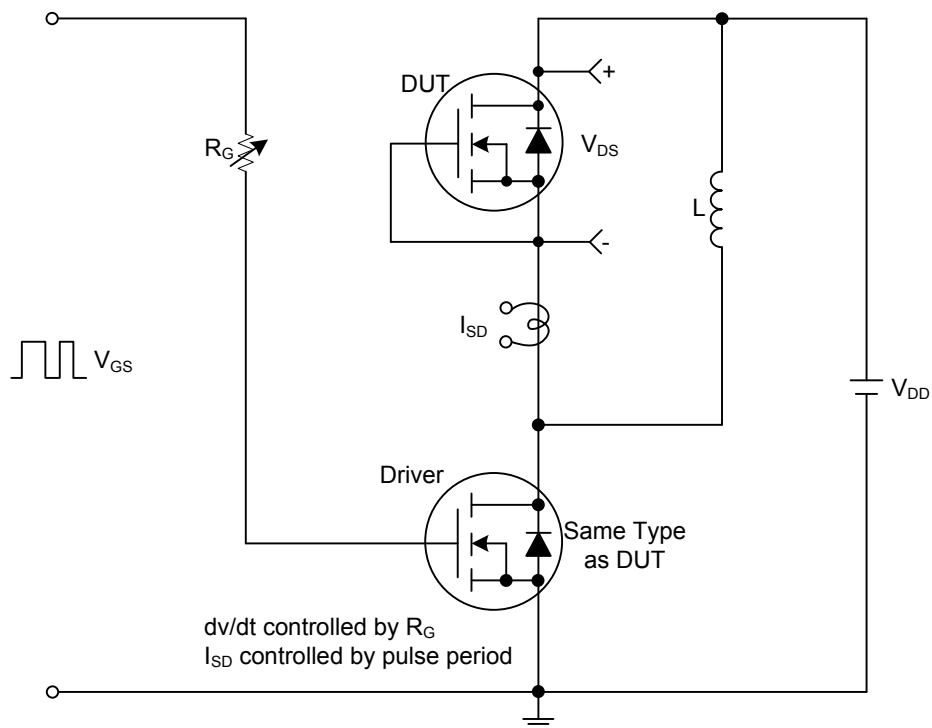


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)



Peak Diode Recovery dv/dt Test Circuit and Waveforms

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